Final datasheet

CoolSiC™ 1400 V SiC MOSFET G2 : Silicon Carbide MOSFET with .XT interconnection technology

Eigenschaften



- V_{DSS} = 1400 V at T_{vj} = 25°C
- I_{DDC} = 37 A at T_C = 100°C
- $R_{DS(on)}$ = 38 mΩ at V_{GS} = 18 V, T_{vj} = 25°C
- Very low switching losses
- Short circuit withstand time 2 µs
- Benchmark gate threshold voltage, $V_{GS(th)}$ = 4.2 V
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Geeignete Infineon Gate-Treiber finden Sie unter https://www.infineon.com/gdfinder

Halogen-free

Green

Lead-free

RoHS

Potenzielle Anwendungen

- General purpose drives (GPD)
- EV Charging
- Online UPS / Industrial UPS
- String inverter
- Energy storage systems (ESS)
- Welding

Produktvalidierung

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Beschreibung

Pin definition:

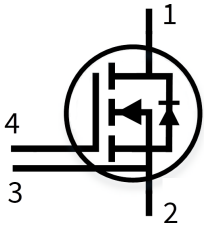
• Pin 1 – Drain

• Pin 2 – Source

• Pin 3 – Kelvin sense contact

• Pin 4 – Gate

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction



Type	Package	Marking
IMZC140R038M2H	PG-TO247-4-U07	14M2H038

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1 Gehäuse

Tabelle 1 Charakteristische Werte

Parameter	Symbol	Notiz oder Prüfbedingung	Werte			Einh.
			Min	Typ	Max	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	Wave soldering only allowed at leads 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.47	0.62	K/W

2 MOSFET

Tabelle 2 Höchstzulässige Werte

Parameter	Symbol	Notiz oder Prüfbedingung		Werte	Einh.
Drain-Source-Spannung	V_{DSS}	$T_{vj} \geq 25$ °C		1400	V
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18$ V	$T_c = 25$ °C	52	A
			$T_c = 100$ °C	37	
Peak drain current, t_p limited by $T_{vj(max)}$ [1)]	I_{DM}	$V_{GS} = 18$ V		185	A
Gate-source voltage, max. transient voltage	V_{GS}	$t_p \leq 0.5$ µs, $D < 0.01$		-10...25	V
Gate-source voltage, max. static voltage [2)]	V_{GS}			-7...23	V
Avalanche energy, single pulse	E_{AS}	$I_D = 20.4$ A, $V_{DD} = 50$ V, $L = 1.2$ mH, $T_{vj(start)} = 25$ °C		255	mJ
Avalanche energy, repetitive	E_{AR}	$I_D = 20.4$ A, $V_{DD} = 50$ V, $L = 6.2$ µH, $T_{vj(start)} = 25$ °C		1.3	mJ
Short-circuit withstand time	t_{SC}	$V_{DD} \leq 800$ V, $V_{DS,peak} < 1400$ V, $V_{GS(on)} = 15$ V, $T_{vj(start)} = 25$ °C		2	µs
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25$ °C	242	W
			$T_c = 100$ °C	121	

1) Verified by design.
2) The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

Tabelle 3 Empfohlene Werte

Parameter	Symbol	Notiz oder Prüfbedingung	Werte	Einh.
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

Tabelle 4 Charakteristische Werte

Parameter	Symbol	Notiz oder Prüfbedingung		Werte			Einh.
				Min	Typ	Max	
Drain-source on-state resistance	$R_{DS(on)}$	I_D = 20.4 A	T_{vj} = 25 °C, $V_{GS(on)}$ = 18 V		38		mΩ
			T_{vj} = 150 °C, $V_{GS(on)}$ = 18 V		81.3	106.5	
			T_{vj} = 175 °C, $V_{GS(on)}$ = 18 V		94		
			T_{vj} = 25 °C, $V_{GS(on)}$ = 15 V		47		
Gate-source threshold voltage	$V_{GS(th)}$	I_D = 6.4 mA, V_{DS} = V_{GS} (tested after 1 ms pulse at V_{GS} = 20 V)	T_{vj} = 25 °C	3.5	4.2	5.1	V
			T_{vj} = 175 °C		3.2		
Zero gate-voltage drain current	I_{DSS}	V_{DS} = 1400 V, V_{GS} = 0 V	T_{vj} = 25 °C			150	µA
			T_{vj} = 175 °C		2.6		
Gate leakage current	I_{GSS}	V_{DS} = 0 V	V_{GS} = 23 V			120	nA
			V_{GS} = -10 V			-120	
Forward transconductance	g_{fs}	I_D = 20.4 A, V_{DS} = 20 V			13		S
Internal gate resistance	$R_{G,int}$	f = 1 MHz, V_{AC} = 25 mV			2.75		Ω
Input capacitance	C_{iss}	V_{DS} = 1000 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			1480		pF
Output capacitance	C_{oss}	V_{DS} = 1000 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			50		pF
Reverse transfer capacitance	C_{rss}	V_{DS} = 1000 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			4.5		pF
C_{oss} stored energy	E_{oss}	Calculated based on C_{oss} = f(V_{DD})			32		µJ
Output charge	Q_{oss}	Calculated based on C_{oss} = f(V_{DD})			87		nC
Effective output capacitance, energy related	$C_{o(er)}$	V_{DS} = 0...1000 V, V_{GS} = 0 V, Calculated based on E_{oss}			99		pF
Effective output capacitance, time related	$C_{o(tr)}$	I_D = constant, V_{DS} = 0...1000 V, V_{GS} = 0 V, Calculated based on Q_{oss}			109		pF

(wird fortgesetzt...)

Tabelle 4 (Fortsetzung) Charakteristische Werte

Parameter	Symbol	Notiz oder Prüfbedingung		Werte			Einh.
				Min	Typ	Max	
Total gate charge	Q_G	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, turn-on pulse			41		nC
Plateau gate charge	$Q_{GS(pl)}$	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, turn-on pulse			11.6		nC
Gate-drain charge	Q_{GD}	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, turn-on pulse			10.6		nC
Turn-on delay time	$t_{d(on)}$	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		5.3		ns
			T_{vj} = 175 °C		4.6		
Rise time	t_r	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		3.1		ns
			T_{vj} = 175 °C		2.9		
Turn-off delay time	$t_{d(off)}$	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		13		ns
			T_{vj} = 175 °C		14		
Fall time	t_f	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		5.1		ns
			T_{vj} = 175 °C		5.6		
Turn-on energy	E_{on}	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		153		µJ
			T_{vj} = 175 °C		504		
Turn-off energy	E_{off}	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		50		µJ
			T_{vj} = 175 °C		58		
Total switching energy[1)]	E_{tot}	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		268		µJ
			T_{vj} = 175 °C		838		

(wird fortgesetzt...)

Tabelle 4 (Fortsetzung) Charakteristische Werte

Parameter	Symbol	Notiz oder Prüfbedingung		Werte			Einh.
				Min	Typ	Max	
Turn-on energy at -5 V	E_{on}	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = -5/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = -5 V	T_{vj} = 25 °C		153		µJ
			T_{vj} = 175 °C		519		
Turn-off energy at -5 V	E_{off}	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = -5/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = -5 V	T_{vj} = 25 °C		32		µJ
			T_{vj} = 175 °C		32		
Total switching energy at -5 V[1)]	E_{tot}	V_{DD} = 1000 V, I_D = 20.4 A, V_{GS} = -5/18 V, $R_{G,ext}$ = 2.3 Ω, L_σ = 12 nH, diode: body diode at V_{GS} = -5 V	T_{vj} = 25 °C		250		µJ
			T_{vj} = 175 °C		835		
Virtual junction temperature	T_{vj}			-55		175	°C

1) including E_{fr}

***Hinweis**: The chip technology was characterized up to 200 kV/µs. The measured dV/dt was limited by measurement test setup and package.*

Characteristics at T_{vj} = 25°C, unless otherwise specified.

3 Body diode (MOSFET)

Tabelle 5 Höchstzulässige Werte

Parameter	Symbol	Notiz oder Prüfbedingung		Werte	Einh.
Drain-source voltage	V_{DSS}	T_{vj} ≥ 25 °C		1400	V
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{SDC}	V_{GS} = 0 V	T_c = 25 °C	43	A
			T_c = 100 °C	24	
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	V_{GS} = 0 V		111	A

Tabelle 6 Charakteristische Werte

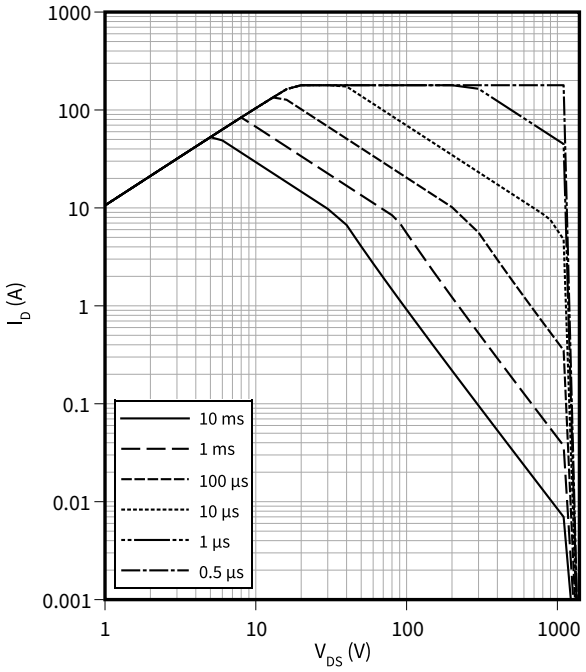
Parameter	Symbol	Notiz oder Prüfbedingung		Werte			Einh.
				Min	Typ	Max	
Drain-source reverse voltage	V_{SD}	I_{SD} = 20.4 A, V_{GS} = 0 V	T_{vj} = 25 °C		4.2	5.5	V
			T_{vj} = 100 °C		4.11		
			T_{vj} = 175 °C		4.05		
MOSFET forward recovery charge	Q_{fr}	V_{DD} = 1000 V, I_{SD} = 20.4 A, V_{GS} = 0 V, $R_{GS(on)}$ = 2.3 Ω, Q_{fr} includes also Q_C	T_{vj} = 25 °C		0.21		µC
			T_{vj} = 175 °C		0.62		
MOSFET peak forward recovery current	I_{frm}	V_{DD} = 1000 V, I_{SD} = 20.4 A, V_{GS} = 0 V, $R_{GS(on)}$ = 2.3 Ω, Q_{fr} includes also Q_C	T_{vj} = 25 °C		48		A
			T_{vj} = 175 °C		99		
MOSFET forward recovery energy	E_{fr}	V_{DD} = 1000 V, I_{SD} = 20.4 A, V_{GS} = 0 V, $R_{GS(on)}$ = 2.3 Ω, Q_{fr} includes also Q_C	T_{vj} = 25 °C		65		µJ
			T_{vj} = 175 °C		276		
MOSFET forward recovery energy at -5 V	E_{fr}	V_{DD} = 1000 V, I_{SD} = 20.4 A, V_{GS} = -5 V, $R_{GS(on)}$ = 2.3 Ω, Q_{fr} includes also Q_C	T_{vj} = 25 °C		65		µJ
			T_{vj} = 175 °C		284		
Virtual junction temperature	T_{vj}			-55		175	°C

4 Kennlinien

Safe operating area (SOA)

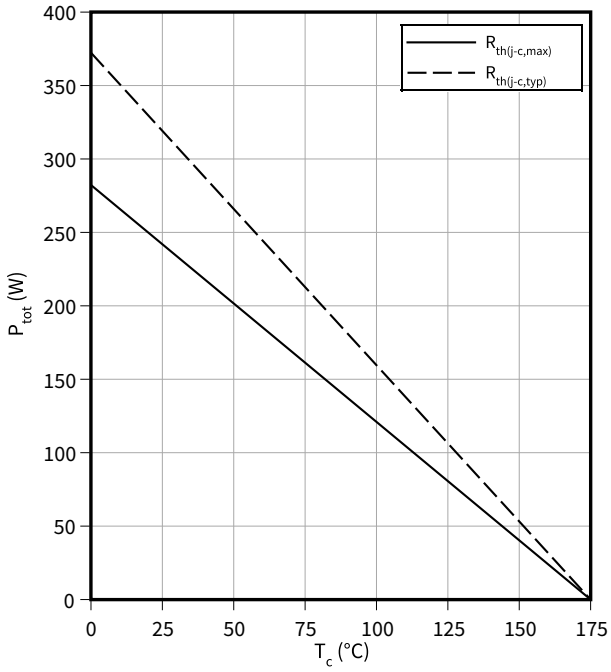
$I_D = f(V_{DS})$

$T_{vj} \leq 175\ °C$, $T_c = 25\ °C$



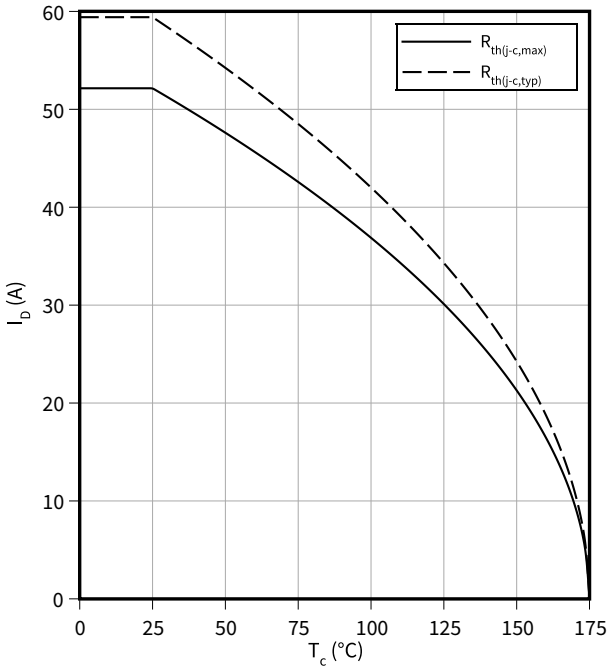
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$



Maximum DC drain to source current as a function of case temperature limited by bond wire

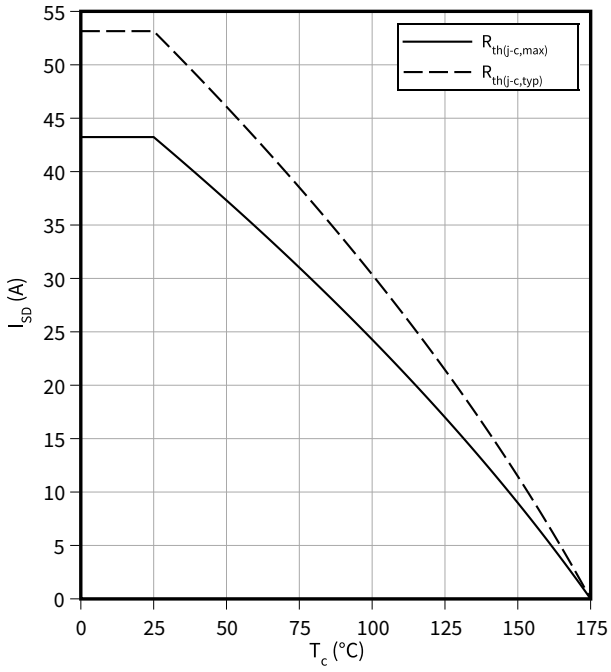
$I_D = f(T_c)$



Maximum source to drain current as a function of case temperature limited by bond wire

$I_{SD} = f(T_c)$

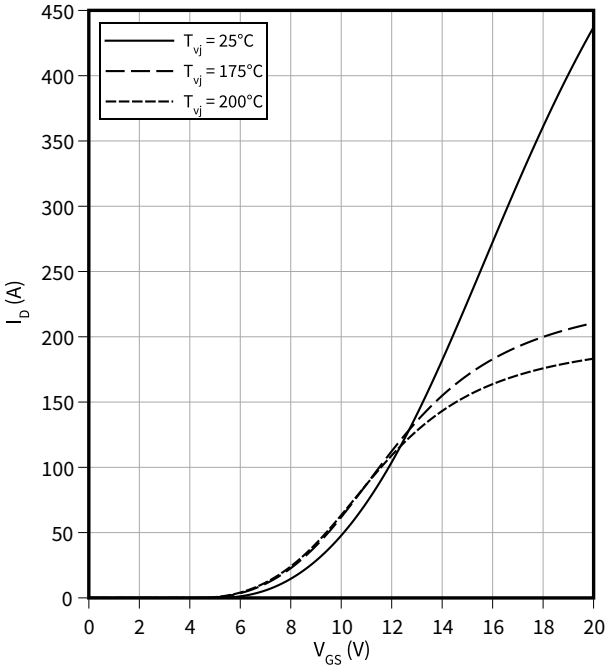
$V_{GS} = 0\ V$



Typical transfer characteristic

$I_D = f(V_{GS})$

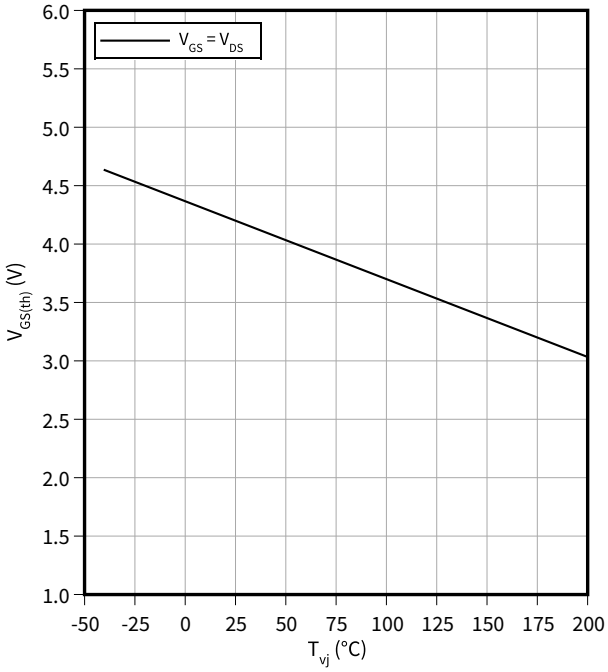
V_{DS} = 20 V, t_p = 20 µs



Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$

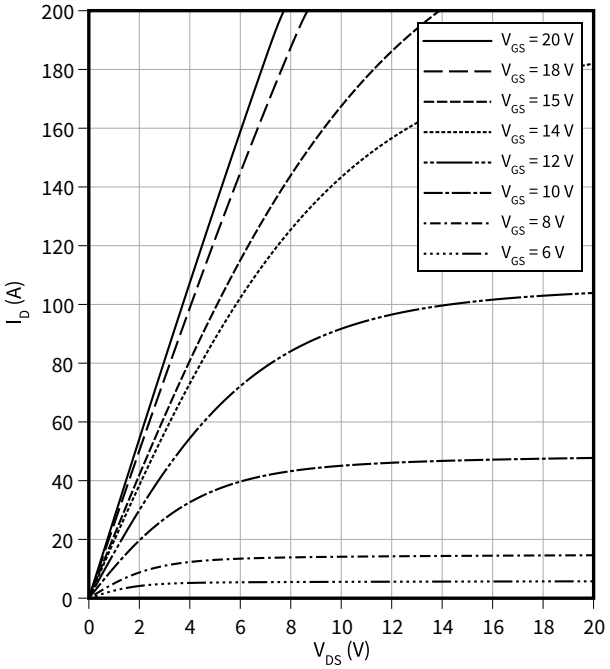
I_D = 6.4 mA



Typical output characteristic, V_{GS} as a parameter

$I_D = f(V_{DS})$

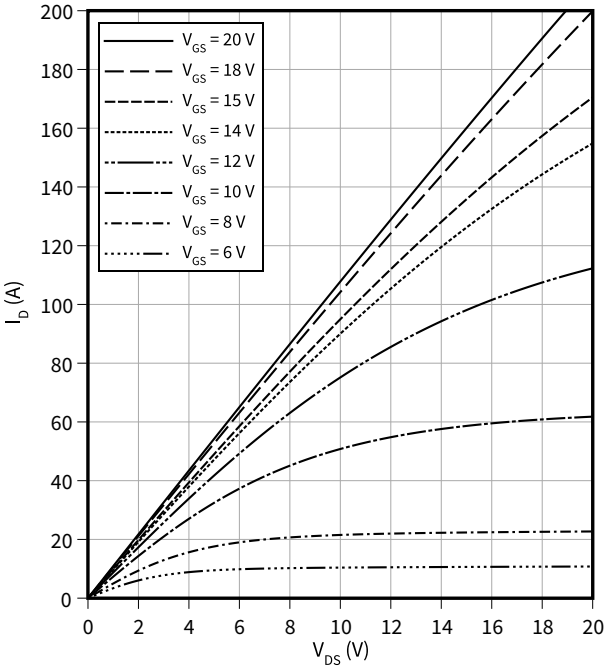
T_{vj} = 25 °C, t_p = 20 µs



Typical output characteristic, V_{GS} as a parameter

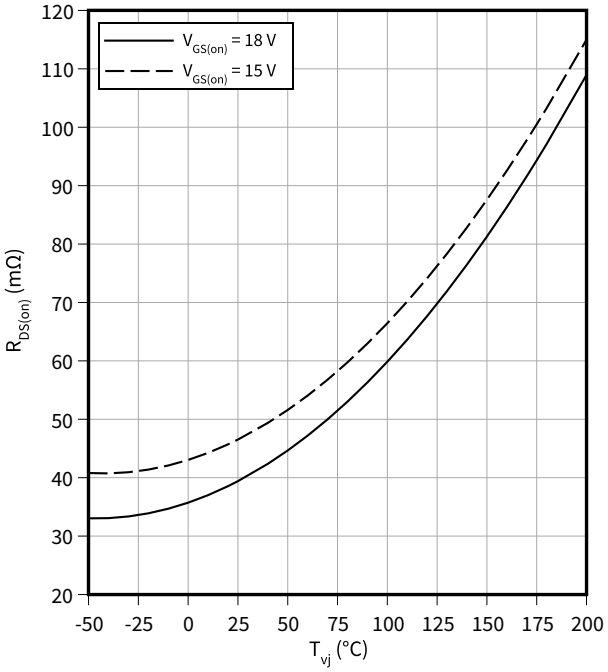
$I_D = f(V_{DS})$

T_{vj} = 175 °C, t_p = 20 µs



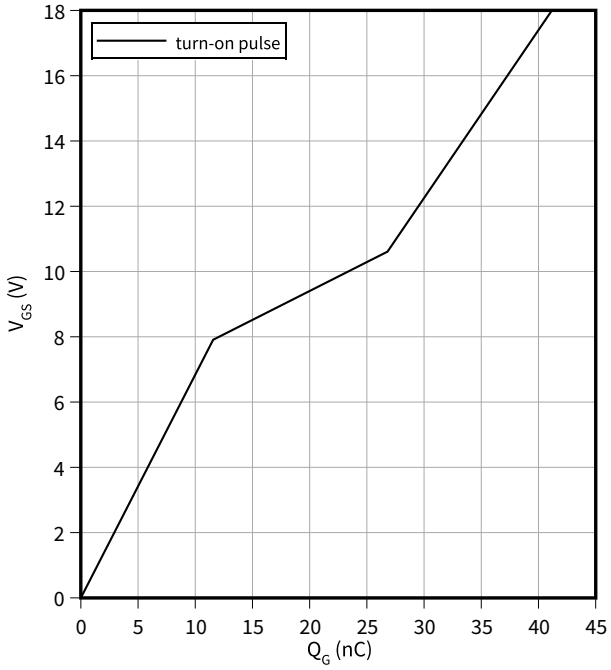
Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$
$I_D = 20.4$ A



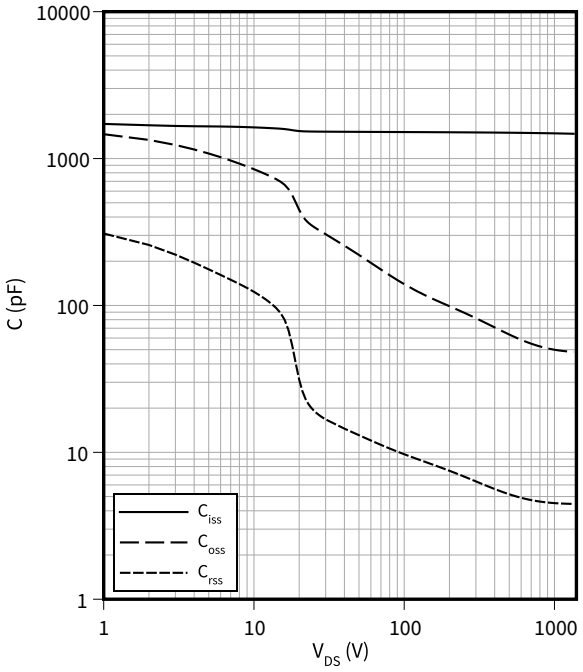
Typical gate charge

$V_{GS} = f(Q_G)$
$I_D = 20.4$ A, $V_{DS} = 1000$ V



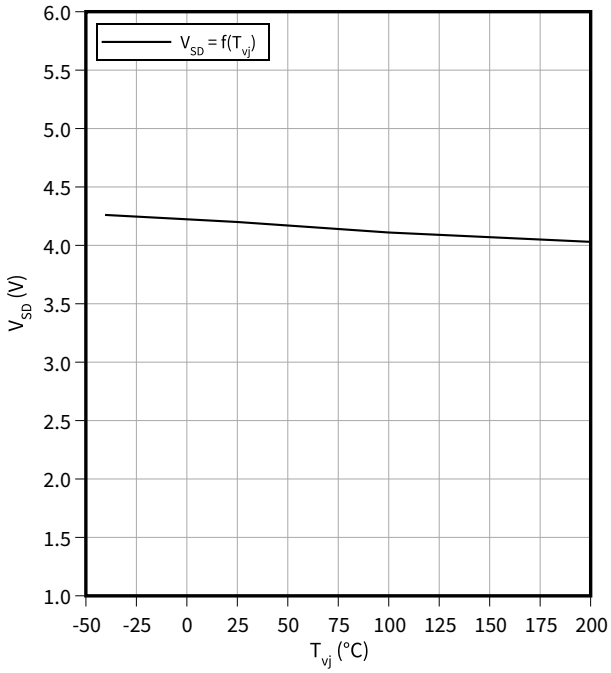
Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$
$f = 100$ kHz, $V_{GS} = 0$ V



Typical reverse drain voltage as a function of junction temperature

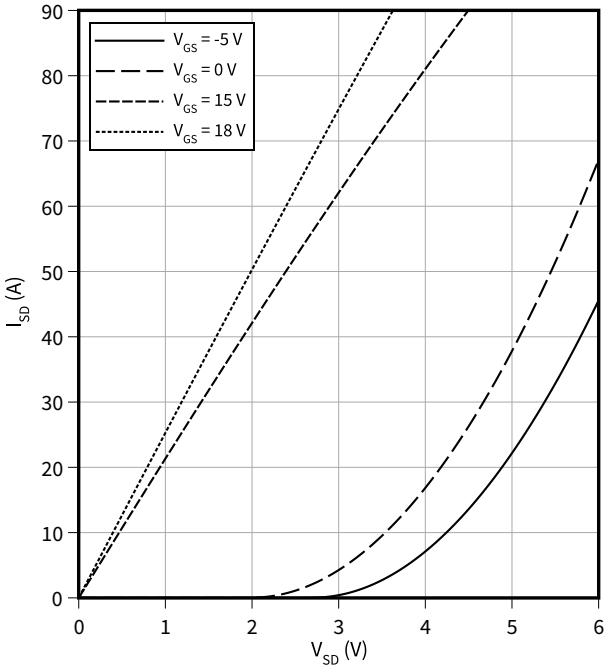
$V_{SD} = f(T_{vj})$
$I_{SD} = 20.4$ A, $V_{GS} = 0$ V



Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$I_{SD} = f(V_{SD})$

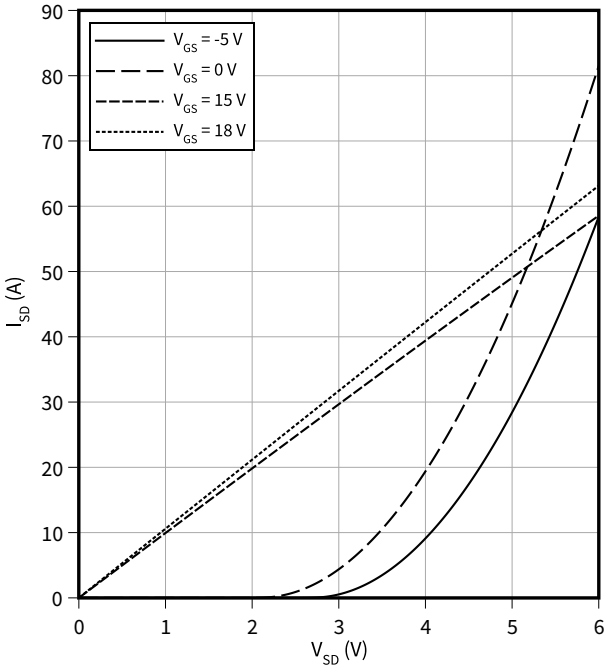
$T_{vj} = 25\ °C$, $t_p = 20\ µs$



Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$I_{SD} = f(V_{SD})$

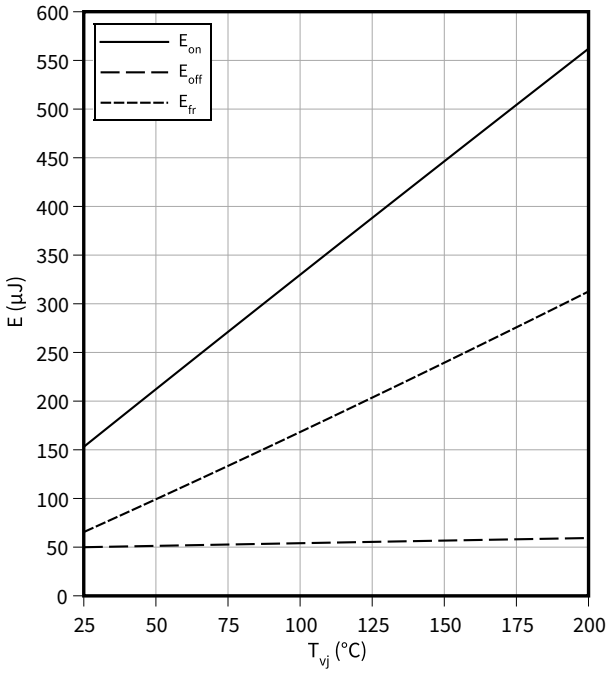
$T_{vj} = 175\ °C$, $t_p = 20\ µs$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\ V$

$E = f(T_{vj})$

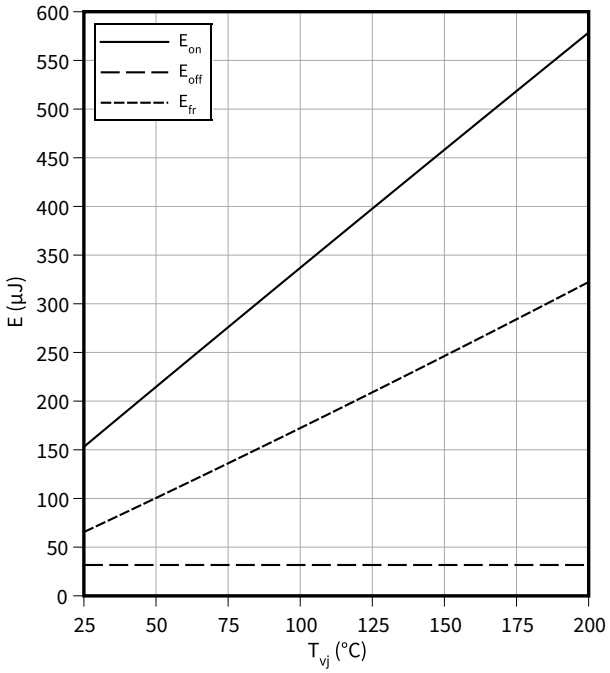
$V_{GS} = 0/18\ V$, $I_D = 20.4\ A$, $R_{G,ext} = 2.3\ Ω$, $V_{DD} = 1000\ V$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\ V$

$E = f(T_{vj})$

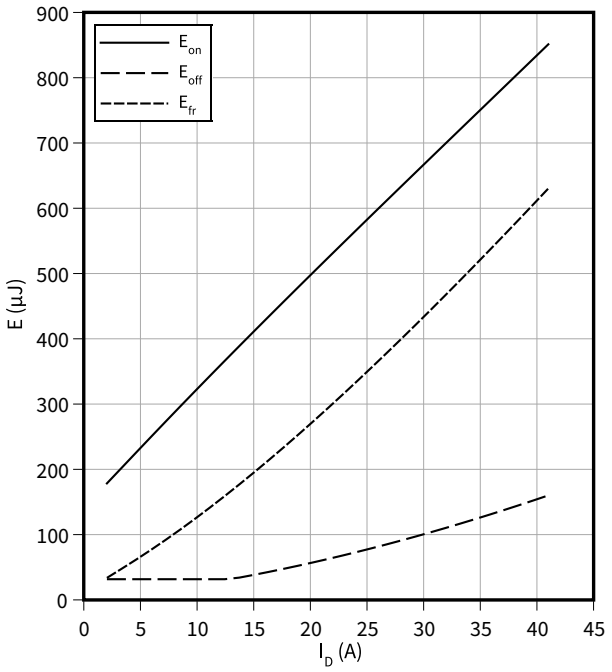
$V_{GS} = -5/18\ V$, $I_D = 20.4\ A$, $R_{G,ext} = 2.3\ Ω$, $V_{DD} = 1000\ V$



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$E = f(I_D)$

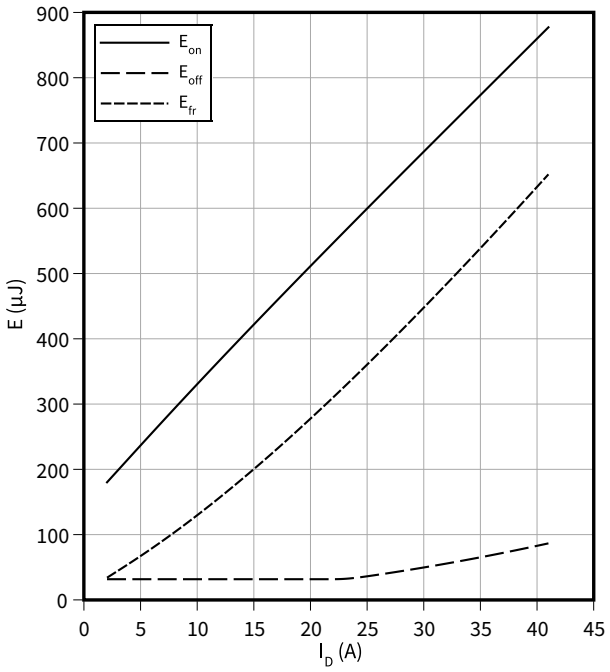
V_{GS} = 0/18 V, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω, V_{DD} = 1000 V



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

$E = f(I_D)$

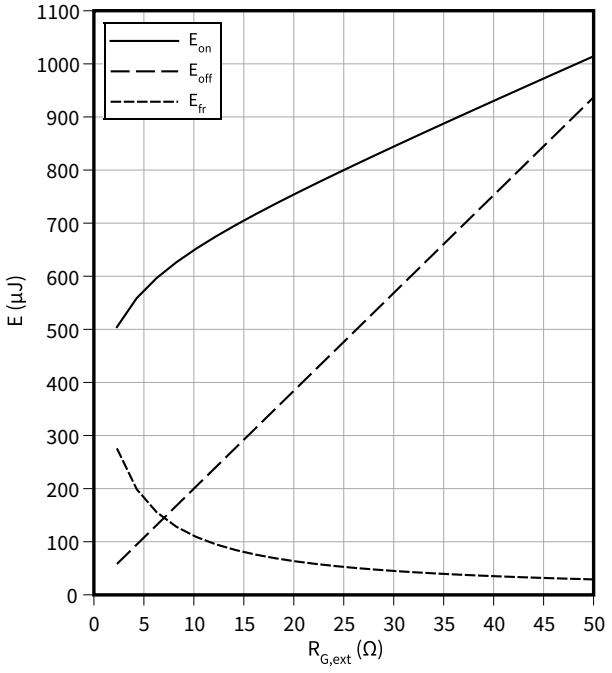
V_{GS} = -5/18 V, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω, V_{DD} = 1000 V



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$E = f(R_{G,ext})$

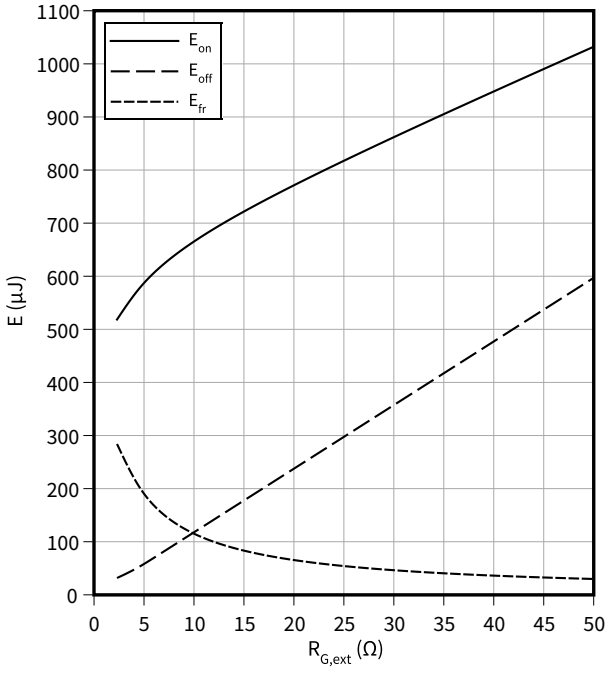
V_{GS} = 0/18 V, I_D = 20.4 A, T_{vj} = 175 °C, V_{DD} = 1000 V



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

$E = f(R_{G,ext})$

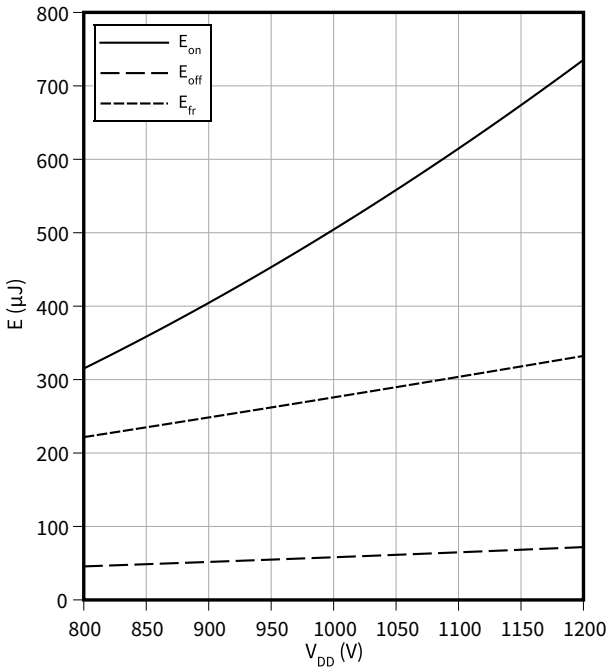
V_{GS} = -5/18 V, I_D = 20.4 A, T_{vj} = 175 °C, V_{DD} = 1000 V



Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

E = f(V_{DD})

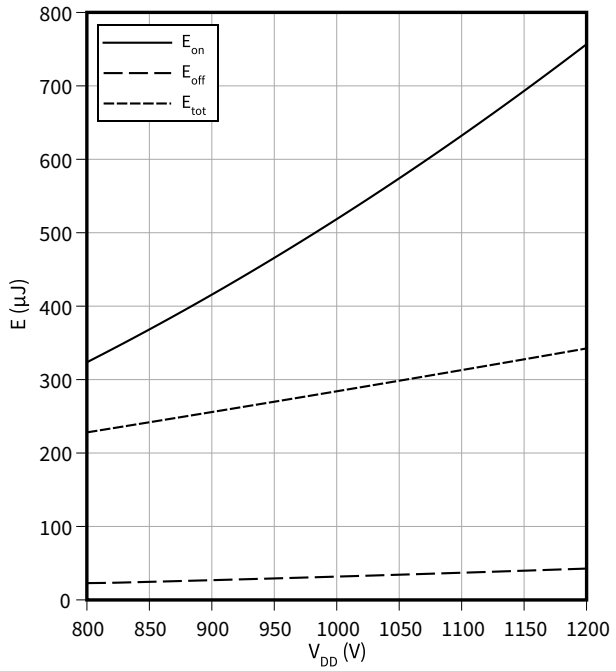
V_{GS} = 0/18 V, I_D = 20.4 A, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω



Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

E = f(V_{DD})

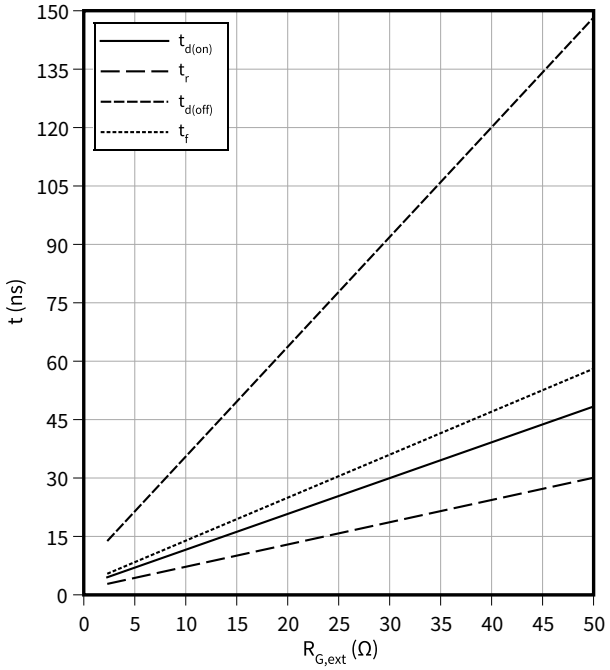
V_{GS} = -5/18 V, I_D = 20.4 A, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

t = f($R_{G,ext}$)

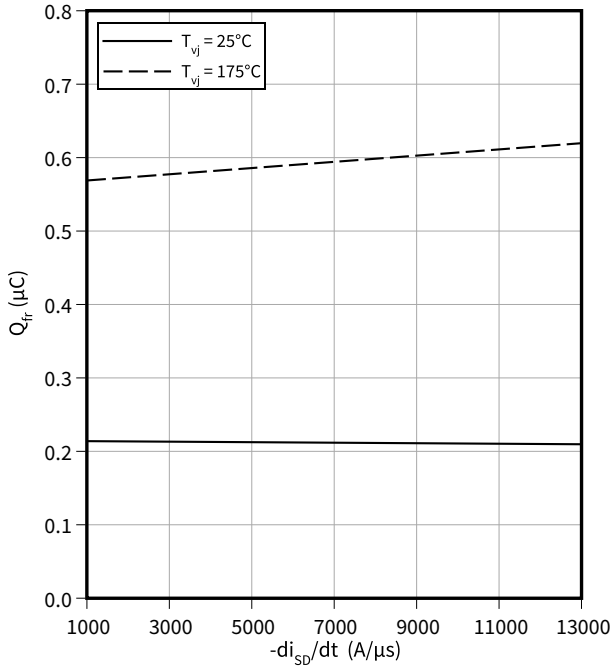
V_{GS} = 0/18 V, I_D = 20.4 A, T_{vj} = 175 °C, V_{DD} = 1000 V



Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

Q_{fr} = f(-di_{SD}/dt)

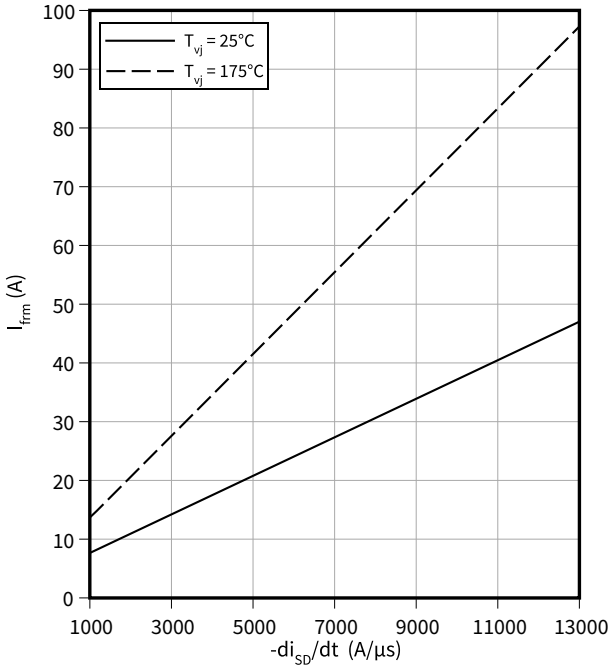
V_{GS} = 0/18 V, I_{SD} = 20.4 A, V_{DD} = 1000 V



Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$I_{frm} = f(-di_{SD}/dt)$

V_{GS} = 0/18 V, I_{SD} = 20.4 A, V_{DD} = 1000 V

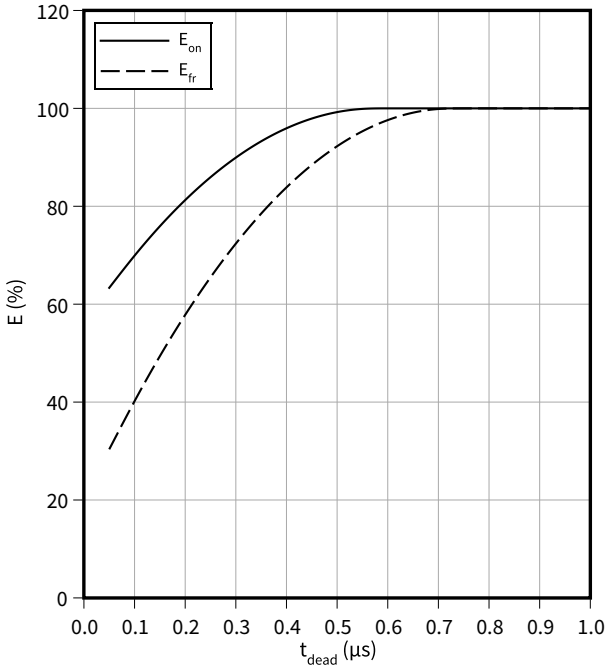


Typical switching energy as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$E = f(t_{dead})$

V_{GS} = 0/18 V, I_D = 20.4 A, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω

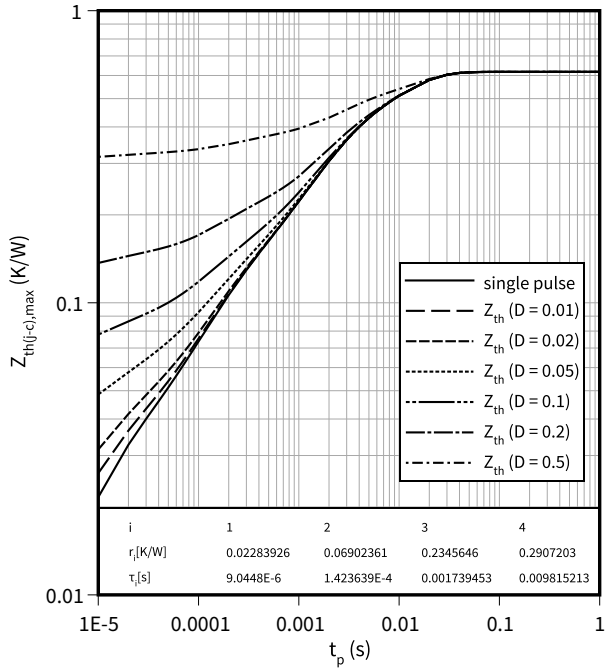
V_{DD} = 1000 V



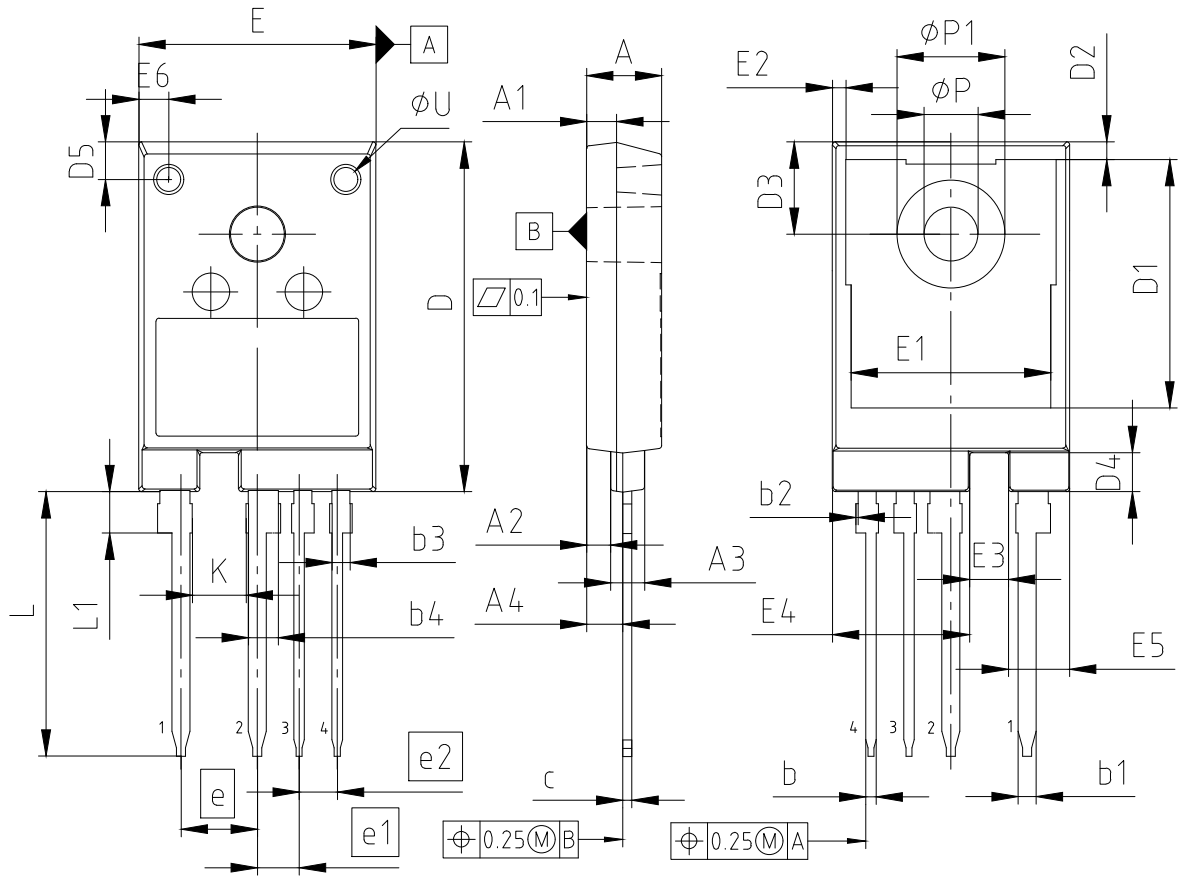
Max. transient thermal impedance (MOSFET/diode)

$Z_{th(j-c),max} = f(t_p)$

$D = t_p/T$



5 Gehäuseabmessungen



PACKAGE - GROUP NUMBER:	PG-TO247-4-U07				
DIMENSIONS	**MILLIMETERS**		**DIMENSIONS**	**MILLIMETERS**	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	**E**	15.60	16.00
A1	1.90	2.10	**E1**	13.10	13.50
A2	1.50	1.70	**E2**	0.60	1.20
A3	2.16	2.36	**E3**	2.48	2.68
A4	2.31	2.51	**E4**	9.05	9.25
b	0.60	0.80	**E5**	3.97	4.17
b1	1.10	1.30	**E6**	1.80	2.20
b2	---	0.15	**e**	5.08	
b3	1.10	1.30	**e1**	2.79	
b4	1.90	2.10	**e2**	2.54	
c	0.50	0.70	**K**	3.50	---
D	23.10	23.50	**L**	17.50	17.80
D1	16.25	16.85	**L1**	2.61	2.91
D2	0.97	1.37	**N**	4	
D3	6.00	6.30	**ØP1**	7.00	7.40
D4	2.50	2.70	**ØP**	3.50	3.70
D5	2.30	2.70	**ØU**	1.40	1.80

NOTES: DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS
N IS THE NUMBER OF LEADS

Abbildung 1

6 Testing conditions

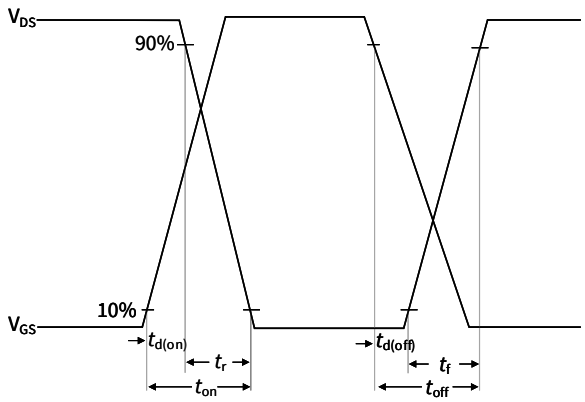


Figure A. **Definition of switching times**

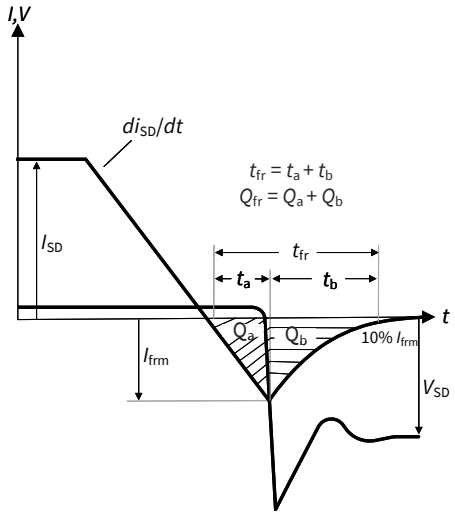


Figure B. **Definition of body diode switching characteristics**

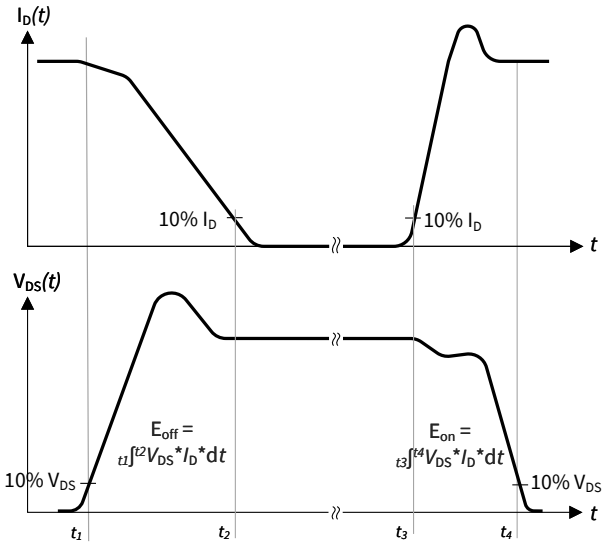


Figure C. **Definition of switching losses**

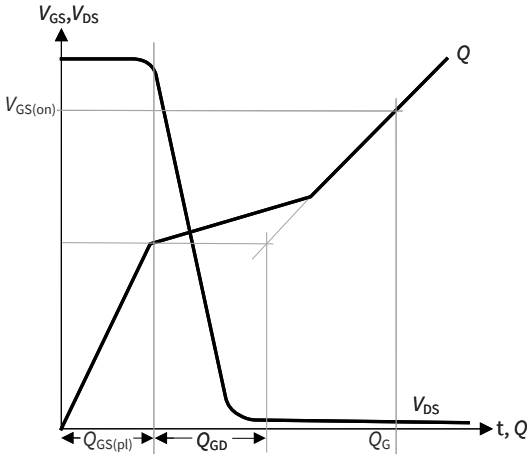


Figure D. **Definition of QGD**

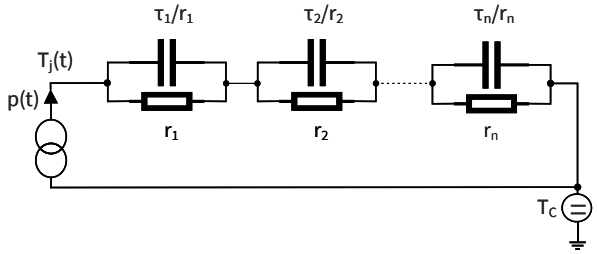


Figure E. **Thermal equivalent circuit**

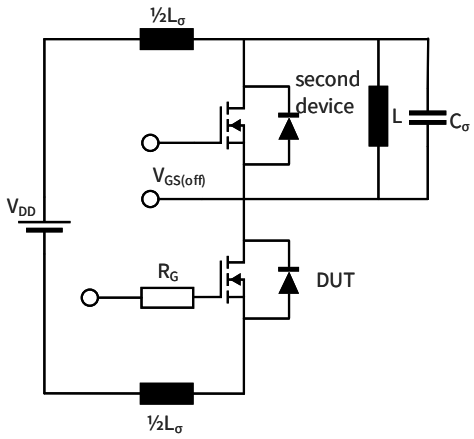


Figure F. **Dynamic test circuit**
Parasitic inductance L_σ,
Parasitic capacitor C_σ,

Abbildung 2

Änderungshistorie

Dokumentenrevision	Freigabedatum	Beschreibung der Änderungen
0.10	2025-05-28	Preliminary datasheet
1.00	2025-06-12	Final datasheet

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